10/536696 JC06 Rec CT/PTO 27 MAY 2005

Docket No.: 4590-410 PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

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Arnaud GRISARD et al.

U.S. Patent Application No. not yet assigned

Filed: herewith

For: METHOD OF PRODUCING THICK NON-LINEAR OPTICAL GRATINGS

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed with the application and no certification or fee is required.

Please note this is a PCT application in the entry of the National Phase in the U.S. and copies of the references cited were transmitted by WIPO and are believed to be in the file of the above-identified application and readily available to the Examiner. Therefore it is believed that Applicants have met all requirements regarding duty of disclosure under 37 CFR 1.56. A copy of the foreign search report is attached for the Examiner's information. Acknowledgement and consideration of these documents are respectfully requested.

Respectfully submitted,

LOWE HAUPTMAN & BERNER, LLP

Randy A Noranbrock for Kenneth M. Berner Registration No. 42,940 Registration No. 37,093

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Date: May 27, 2005

JC05 Rec'd PCT/PTO 27 MAY 2005 Sheet 1 of 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 4590-410		U.S. APPLICATION NO.	
				APPLICANT Arnaud GRISARD et al.			
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	Eyres L A et al: All Epitaxial Fabrication of Thick, Orientation-Patterned Gaas Films for Nonlinear Optical Frequency Conversion" Applied Physics Letters, American Institute of Physics, New York, August 13, 2001						
<b>EXAMINER</b>		ATE CONSIDERED					

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.